SK80GM063



IGBT Module

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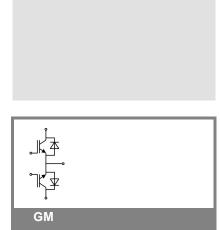
Preliminary Data

Features

- Compact design
- · One screw mounting
- Heat transfer and isolation through direct copper bonded aluminium oxide ceramic (DCB)
- High short circuit capability
- Low tail current with low temperature dependence

Typical Applications*

- Switching (not for linear use)
- Inverter
- Switched mode power supplies
- UPS



Absolute Maximum Ratings $T_s = 25 ^{\circ}\text{C}$, unless otherwise specified					
Symbol	Conditions		Values	Units	
IGBT	•			•	
V_{CES}	T _j = 25 °C		600	V	
I _C	T _j = 125 °C	T _s = 25 °C	81	Α	
		$T_s = 80 ^{\circ}C$	57	Α	
I _{CRM}	I _{CRM} = 2 x I _{Cnom}		200	Α	
V_{GES}			± 20	V	
t _{psc}	V_{CC} = 300 V; $V_{GE} \le 20$ V; VCES < 600 V	T _j = 125 °C	10	μs	
Inverse D	iode				
I _F	T _j = 150 °C	$T_s = 25 ^{\circ}C$	105	Α	
		$T_s = 80 ^{\circ}C$	75	Α	
I _{FRM}	I _{FRM} = 2 x I _{Fnom}			Α	
I _{FSM}	t _p = 10 ms; half sine wave	T _j = 150 °C	880	Α	
Module					
I _{t(RMS)}				Α	
T_{vj}			-40 +150	°C	
T _{stg}			-40 +1 25	°C	
V _{isol}	AC, 1 min.		2500	V	

Characteristics $T_s =$			25 °C, unless otherwise specified			
Symbol	Conditions		min.	typ.	max.	Units
IGBT						
$V_{GE(th)}$	$V_{GE} = V_{CE}$, $I_C = 2 \text{ mA}$		4,5	5,5	6,5	V
I _{CES}		T _j = 25 °C			0,3	mA
	V _{CE} = 0 V, V _{GE} = 30 V	T _j = 125 °C				mA
I _{GES}	V _{CE} = 0 V, V _{GE} = 30 V	T _j = 25 °C			240	nA
		T _j = 125 °C				nA
V_{CE0}		T _j = 25 °C		0,9		V
		T _j = 125 °C		0,9		V
r_{CE}	V _{GE} = 15 V	T _j = 25°C		11		mΩ
		T _j = 125°C		15		mΩ
V _{CE(sat)}	I _{Cnom} = 100 A, V _{GE} = 15 V			2	2,5	V
		$T_j = 125^{\circ}C_{chiplev.}$		2,4		V
C _{ies}				4,4		nF
C _{oes}	V _{CE} = 25, V _{GE} = 0 V	f = 1 MHz				nF
C _{res}				0,4		nF
Q_G	V _{GE} =0 20 V			310		nC
t _{d(on)}				45	60	ns
t _r	$R_{Gon} = 11 \Omega$	V _{CC} = 300V		35	50	ns
Ė _{on}	D -44.0	I _C = 60A		3	200	mJ
t _{d(off)}	R_{Goff} = 11 Ω	T _j = 125 °C		250 25	300 40	ns
t _f ⊏		V _{GE} =±15V		2,3	40	ns mJ
E _{off}				۷,۵		
$R_{th(j-s)}$	per IGBT				0,6	K/W

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SEMITOP® 2

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Typical Applications*

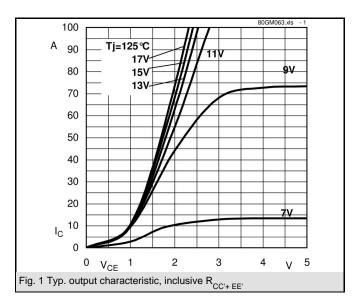
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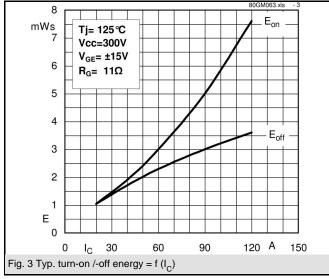
Characteristics							
Symbol	Conditions		min.	typ.	max.	Units	
Inverse Diode							
$V_F = V_{EC}$	I_{Fnom} = 60 A; V_{GE} = 0 V	T _j = 25 °C _{chiplev.}		1,3	1,5	V	
		$T_j = 125 ^{\circ}C_{chiplev.}$		1,2	1,45	V	
V_{F0}		T _j = 125 °C		0,85	0,9	V	
r _F		T _j = 125 °C		5,8	7,5	mΩ	
I _{RRM}	I _F = 60 A	T _i = 125 °C		22	26	Α	
Q_{rr}	$di/dt = -500 A/\mu s$,		2,2	3,5	μC	
E _{rr}	V _{CC} = 300V			0,2	0,3	mJ	
$R_{th(j-s)D}$	per diode				1,2	K/W	
M_s	to heat sink M1				2	Nm	
w				21		g	

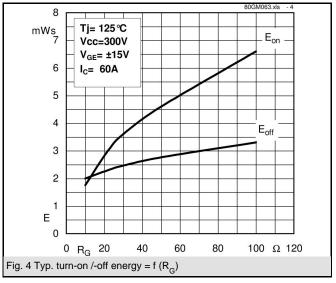
This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

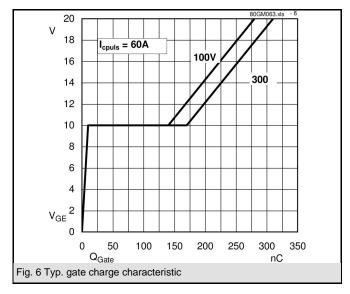
* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.











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